

### Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

#### Listing of Claims:

Claim 1 (currently amended): A target and backing plate assembly for use in magnetron sputtering, comprising a copper or copper alloy target [/] and a copper alloy backing plate assembly ~~for use in magnetron sputtering, wherein~~ the copper alloy backing plate ~~is being~~ formed from a material selected from a group consisting of low beryllium copper alloy containing 0.2 to 0.5wt% of Be, ~~or~~ Cu-Ni-Si containing 2 to 4wt% of Ni and 0.3 to 0.9wt% of Si, and ~~or~~ Cu-Ni-Si-based alloy containing 2 to 4wt% of Ni and 0.3 to 0.9wt% of Si.

Claim 2 (currently amended): The ~~copper or copper alloy target/copper alloy backing plate~~ assembly according to claim 1, wherein the backing plate is a Cu-Ni-Si-based alloy backing plate ~~is~~ formed from Cu-Ni-Si-based alloy containing 2 to 4wt% of Ni, 0.3 to 0.9wt% of Si, 0.1 to 0.9wt% of Cr or 0.1 to 0.9wt% of Mg.

Claims 3-6 (canceled).

Claim 7 (new): An assembly according to claim 2, wherein the copper alloy backing plate has an electrical conductivity of 35 to 60% (IACS), and 0.2% proof stress of 400 to 850MPa.

Claim 8 (new): An assembly according to claim 7, wherein the target and backing plate assembly is diffusion bonded.

Claim 9 (new): An assembly according to claim 8, wherein the diffusion bonded assembly is bonded at a diffusion bonding temperature of 175 to 450°C.

Claim 10 (new): An assembly according to claim 1, wherein the copper alloy backing plate has an electrical conductivity of 35 to 60% (IACS), and 0.2% proof stress of 400 to 850MPa.

Claim 11 (new): An assembly according to claim 10, wherein the target and backing plate assembly is diffusion bonded.

Claim 12 (new): An assembly according to claim 11, wherein the diffusion bonded assembly is bonded at a diffusion bonding temperature of 175 to 450°C.

Claim 13 (new): An assembly according to claim 1, wherein the target and backing plate assembly is diffusion bonded.

Claim 14 (new): An assembly according to claim 11, wherein the diffusion bonded assembly is bonded at a diffusion bonding temperature of 175 to 450°C.